

## **OPTICAL AND ELECTRICAL CHARACTERISTICS OF VACUUM EVAPORATED ZINC TELLURIDE THIN FILMS**

*Arup Kar<sup>1</sup>, Nimisha Neog<sup>2</sup> & P. K. Saikia<sup>3</sup>*

*<sup>1,2</sup>Research Scholar, Department of Physics, Dibrugarh University, Dibrugarh, Assam, India*

*<sup>3</sup>Assistant Professor, Department of Physics, Dibrugarh University, Dibrugarh, Assam, India*

### **ABSTRACT**

*These films of ZnTe compound of varying thickness ranging from 191.3 nm to 248.4 nm have been deposited by vacuum evaporation technique on the clean glass substrates. Optical method (Tolansky method) was employed to measure the thickness of the deposited thin films. The optical properties of the ZnTe thin films were investigated by UV-VIS spectrophotometer and the electrical resistivity have been studied as a function of thickness by Four Probe Kit. The results of all these studied parameters are presented and discussed in this paper.*

**KEYWORDS:** *II–VI Semi-Conductor; Band Gap; Optical Properties; Resistivity; ZnTe Thin Films*

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